

NDL7910P

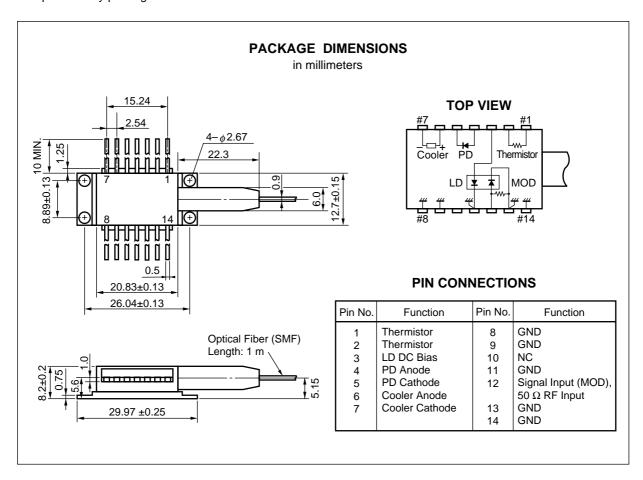
1 550 nm OPTICAL FIBER COMMUNICATIONS EA MODULATOR INTEGRATED MQW-DFB LASER DIODE MODULE FOR 2.5 Gb/s ULTRALONG-REACH APPLICATIONS

DESCRIPTION

The NDL7910P is an EA modulator integrated 1 550 nm DFB-LD for 2.5 Gb/s. The newly developed bandgap energy controlled Selective MOVPE technology is utilized as fabrication method. It is designed for 2.5 Gb/s ultralong-reach applications.

FEATURES

- · Integrated electroabsorption modulator
- · Low modulation voltage
- · Wavelength selectable for ITU-T standards
- · 14-pin butterfly package



The information in this document is subject to change without notice.



ORDERING INFORMATION

Part Number	Available Connector
NDL7910P	Without Connector
NDL7910PC	With FC-PC Connector

ABSOLUTE MAXIMUM RATINGS (Tc = 25 °C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Optical Output Power from Fiber	Pf	10	mW
Forward Current of LD	IFLD	150	mA
Reverse Voltage of LD	V _{RLD}	2.0	V
Forward Voltage of Modulator	V _{Fm}	1	V
Reverse Voltage of Modulator	V _{Rm}	5	V
Forward Current of PD	IFPD	1	mA
Reverse Voltage of PD	V _{RPD}	10	V
Cooler Current	lc	1.5	Α
Cooler Voltage	Vc	2.5	V
Operating Case Temperature	Tc	-20 to +70	°C
Storage Temperature	T _{stg}	-40 to +85	°C
Lead Soldering Temperature (10 s)	Tsld	260	°C

ELECTRO-OPTICAL CHARACTERISTICS

(TLD = 25 °C, Tc = -20 to +70 °C, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating Current	lop		50		100	mA
Modulation Center Voltage	V _{Rmc}		0.5		1.5	V
Modulation Voltage	V _{Rmpp}		2		3	V
Forward Voltage of LD	V _{FLD}	IFLD = lop			1.8	V
Threshold Current	Ith			7	20	mA
Optical Output Power from Fiber	Pf	V _{Rm} = 0 V, I _{FLD} = I _{op}	0.5			mW
Peak Emission Wavelength	λp	IFLD = Iop, VRm = 0 V	1 545		1 560	nm
Spectral Line Width	Δν	IFLD = I₀p, −20 dB, Under modulation*1		4		GHz
Side Mode Suppression Ratio	SMSR	IFLD = Iop, VRm = 0 V	30			dB
Extinction Ratio	ER	IFLD = I₀p, Under modulation*1	10			dB
Cut-off Frequency	fc	I _{FLD} = I _{op} , V _{Rm} = 1/2 V _{Rmpp} , -3 dB, 50Ω	3.2			GHz
Rise Time	tr	IFLD = Iop, 20-80 %, Under modulation*1			125	ps
Fall Time	tf	I _{FLD} = I _{op} , 80-20 %, Under modulation ^{*1}			125	ps
Isolation	Is		30			dB

^{*1 2.48832} Gb/s, PRBS 2 $^{23\text{-1}}$, VRm =VRmc \pm 1/2 VRmpp, NEC Test System

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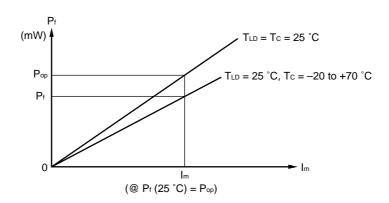


ELECTRO-OPTICAL CHARACTERISTICS

(Applicable to Monitor PD: TLD = 25 °C, Tc = -20 to +70 °C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Monitor Current	Im	I _{FLD} = I _{op} , V _{Rm} = 0 V	20		1 000	μΑ
Dark Current	lσ	VRPD = 5 V			10	nA
Tracking Error	γ*1	Im = const.			0.5	dB
Monitor Capacitance	Ct	V _{RPD} = 5 V, f = 1 MHz			15	pF





ELECTRO-OPTICAL CHARACTERISTICS

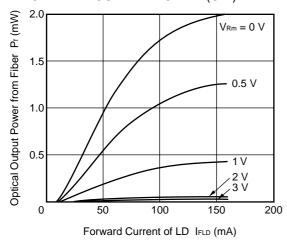
(Applicable to Thermistor and TEC: TLD = 25 °C, Tc = -20 to +70 °C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Thermistor Resistance	R	T _{LD} = 25 °C	9.5	10.0	10.5	kΩ
B Constant	В		3 300	3 400	3 500	К
Cooler Current	lc	$\Delta T = 70 - T_{set}$			1.5	А
Cooler Voltage	Vc	$\Delta T = 70 - T_{set}$			2.5	V

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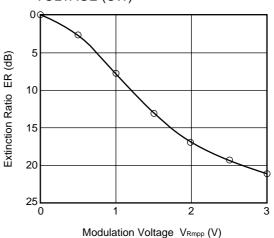
TYPICAL CHARACTERISTICS (TLD = 25 °C, unless otherwise specified)

OPTICAL OUTPUT POWER FROM FIBER vs. FORWARD CURRENT OF LD (CW)



Remark The graphs indicate nominal characteristics.

EXTINCTION RATIO vs. MODULATION VOLTAGE (CW)





★ DFB-LD FAMILY FOR TELECOM

	Absolute Max	imum Ratings	Typical Characteristics				
Part Number	Tc (°C)	T _{stg} (°C)	I _{th} (mA)	P _f (mW)	λc (nm)	SDH Application	Package
			TYP.	MIN.	TYP.		
NDL7603P Series	-40 to +85	-40 to +85	15	2	1 310	≤ STM-4 : 622 Mb/s	Coaxial
NDL7620P Series	0 to +70	-40 to +85	45 (MAX.)	2	1 310	≤ STM-16: 2.5 Gb/s	Coaxial
NDL7701P Series	-20 to +85	-40 to +85	15	2	1 550	≤ STM-4 : 622 Mb/s	Coaxial
NDL7705P Series	-40 to +85	-40 to +85	15	2	1 550	≤ STM-4 : 622 Mb/s	Coaxial
NX8562LB	-20 to +65	-40 to +85	20	20	1 550 ^{*1}	CW Light Source for external modulator	BFY
NX8563LB Series	-20 to +65	-40 to +85	20	10	ITU-T*2	CW Light Source for external modulator	BFY
NDL7910P	-20 to +70	-40 to +85	7	0.5	1 550 ^{*1}	≤ STM-16: 2.5 Gb/s EA modulator integrated DFB-LD	BFY

^{*1} Wavelength selectable for ITU-T standards upon request.

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^{*2} Wavelength selectable for ITU-T standards.



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system	C11159E
Quality grades on NEC semiconductor devices	C11531E
Semiconductor device mounting technology manual	C10535E
Semiconductor selection guide	X10679E

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NEC NDL7910P

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.



SEMICON	IDUCTOR LASER
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AVOID E	XPOSURE-Invisible
Laser Rad	diation is emitted from
this apert	ture

NEC Corporation NEC Building, 7-1, Shiba 5-chome, Minato-ku, Tokyo 108-01, Japan
Type number:
Manufactured:
Serial Number:
This product conforms to FDA
regulations as applicable
o standards 21 CFR Chapter 1.
Subchanter J.

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Anti-radioactive design is not implemented in this product.

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